

AO4828

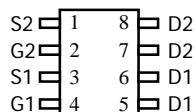
Dual N-Channel Enhancement Mode Field Effect Transistor

General Description

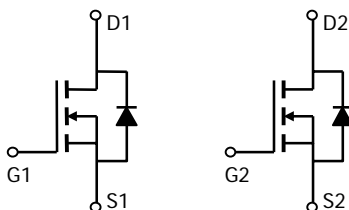
The AO4828 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications. *Standard Product AO4828 is Pb-free (meets ROHS & Sony 259 specifications). AO4828L is a Green Product ordering option. AO4828 and AO4828L are electrically identical.*

Features

V_{DS} (V) = 60V
 I_D = 4.5A (V_{GS} = 10V)
 $R_{DS(ON)}$ < 56m Ω (V_{GS} = 10V)
 $R_{DS(ON)}$ < 77m Ω (V_{GS} = 4.5V)



SOIC-8



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^A	$T_A=25^\circ\text{C}$	4.5	A
Pulsed Drain Current ^B	I_{DM}	20	
Power Dissipation	$T_A=25^\circ\text{C}$	2	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	48	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		Steady-State	74	110
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	35	60	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
B _V DSS	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	60			V
I _D DSS	Zero Gate Voltage Drain Current	V _{DS} =48V, V _{GS} =0V T _J =55°C			1 5	μA
I _G SS	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1	2.1	3	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	20			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =4.5A T _J =125°C		46 80	56 100	mΩ
		V _{GS} =4.5V, I _D =3A		64	77	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =4.5A		11		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.74	1	V
I _S	Maximum Body-Diode Continuous Current				3	A
DYNAMIC PARAMETERS						
C _{ISS}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, f=1MHz		450	540	pF
C _{OSS}	Output Capacitance			60		pF
C _{RSS}	Reverse Transfer Capacitance			25		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		1.65	2	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =30V, I _D =4.5A		8.5	10.5	nC
Q _{g(4.5V)}	Total Gate Charge			4.3	5.5	nC
Q _{gs}	Gate Source Charge			1.6		nC
Q _{gd}	Gate Drain Charge			2.2		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =30V, R _L =6.7Ω, R _{GEN} =3Ω		4.7		ns
t _r	Turn-On Rise Time			2.3		ns
t _{D(off)}	Turn-Off DelayTime			15.7		ns
t _f	Turn-Off Fall Time			1.9		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =4.5A, di/dt=100A/μs		27.5	35	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =4.5A, di/dt=100A/μs		32		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

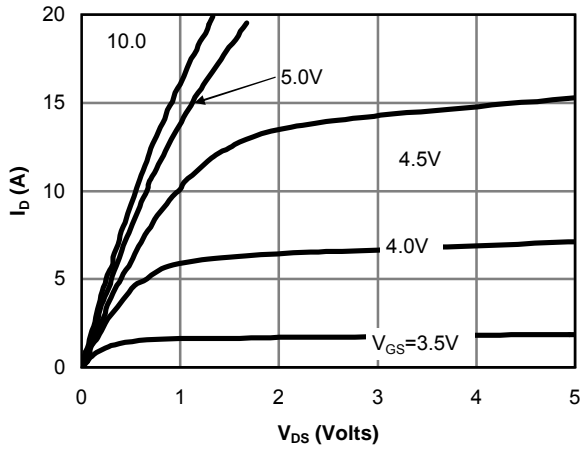


Fig 1: On-Region Characteristics

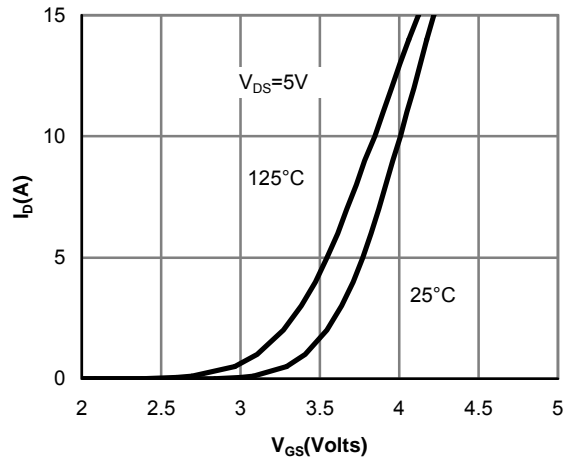


Figure 2: Transfer Characteristics

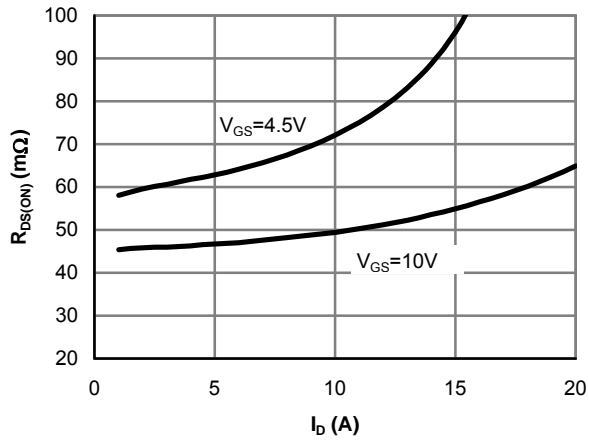


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

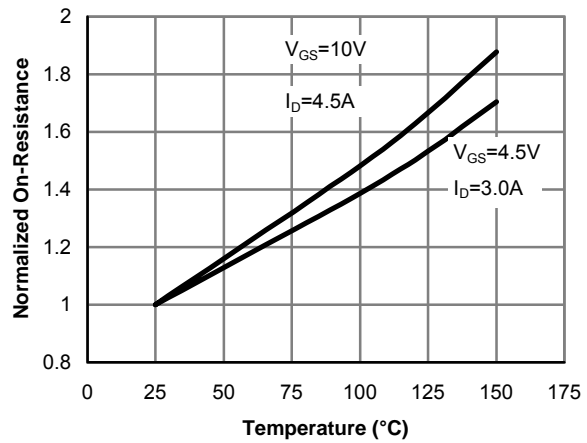


Figure 4: On-Resistance vs. Junction Temperature

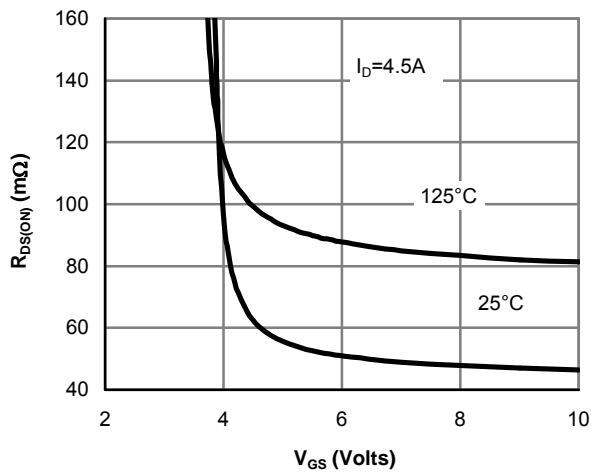


Figure 5: On-Resistance vs. Gate-Source Voltage

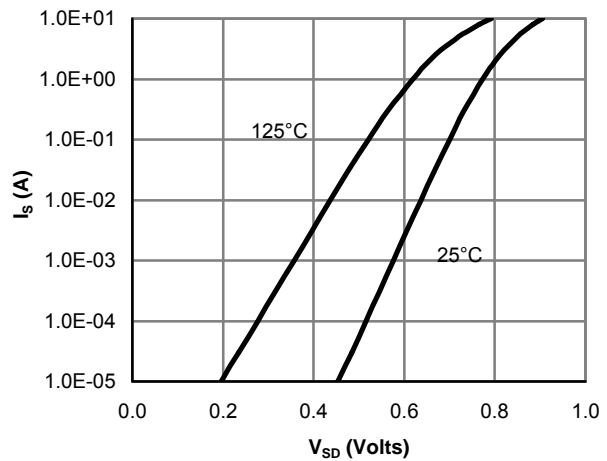


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

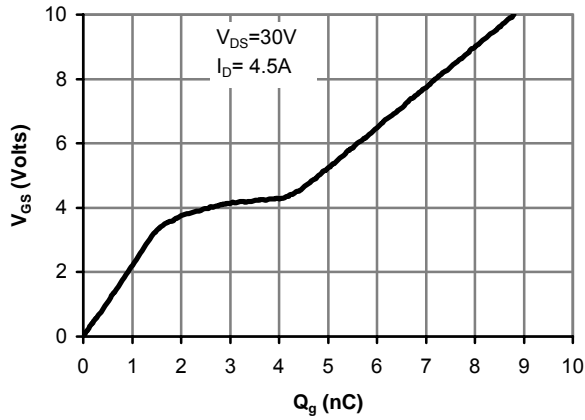


Figure 7: Gate-Charge Characteristics

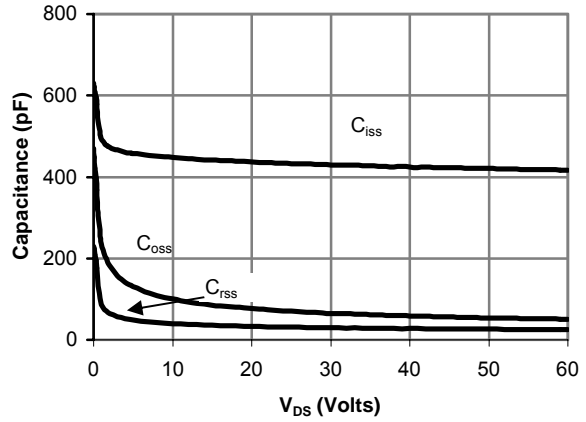


Figure 8: Capacitance Characteristics

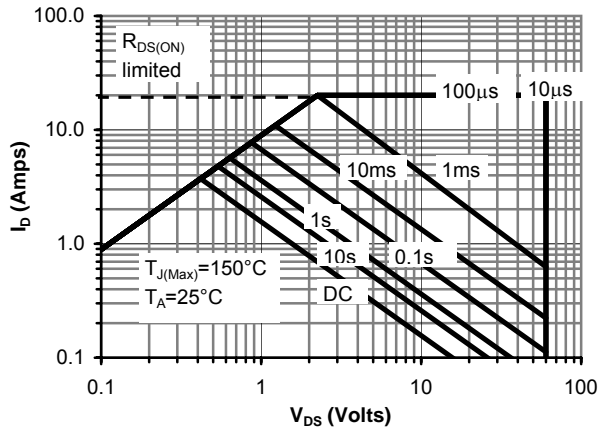


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

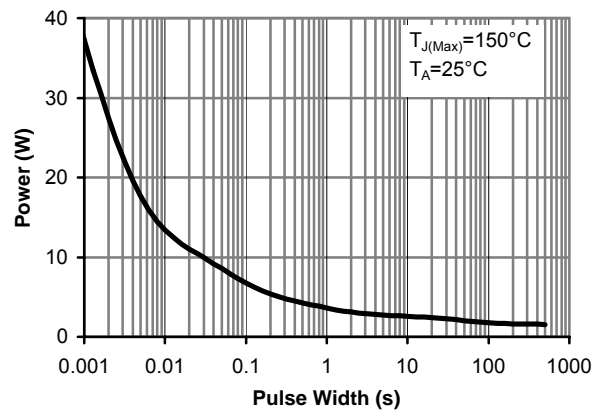


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

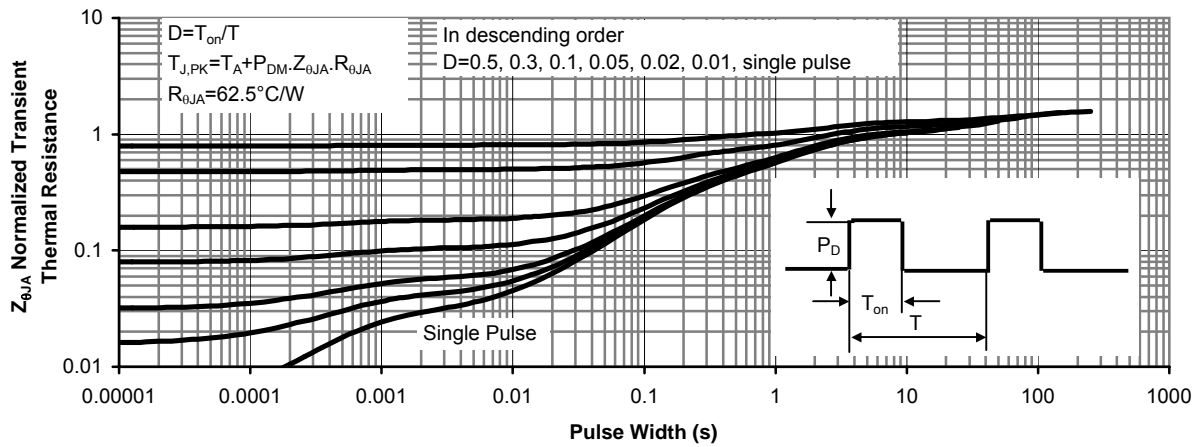


Figure 11: Normalized Maximum Transient Thermal Impedance